

# Switching Diode

## FEATURE

- Small plastic SMD package.
- Continuous reverse voltage: max. 75 V.
- High-speed switching in hybrid thick and thin-film circuits.
- We declare that the material of product compliance with RoHS requirements.

## DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LBAS16BST1G	3*	5000/Tape&Reel
LBAS16BST3G	3*	8000/Tape&Reel
LBAS16BST5G	3*	10000/Tape&Reel

\*Rotated 90°

## MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Continuous Reverse Voltage	$V_R$	75	Vdc
Peak Forward Current	$I_F$	200	mAdc
Peak Forward Surge Current	$I_{FM}(\text{surge})$	500	mAdc

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25^\circ\text{C}$	$P_D$	200	mW
Derate above 25°C		1.57	mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	635	°C/W
Junction and Storage Temperature	$T_J, T_{stg}$	-55to+150	°C

\*\*FR-4 Minimum Pad

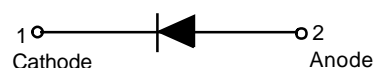
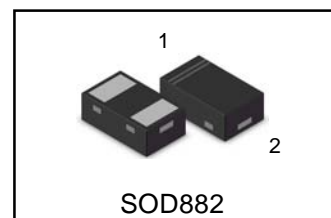
## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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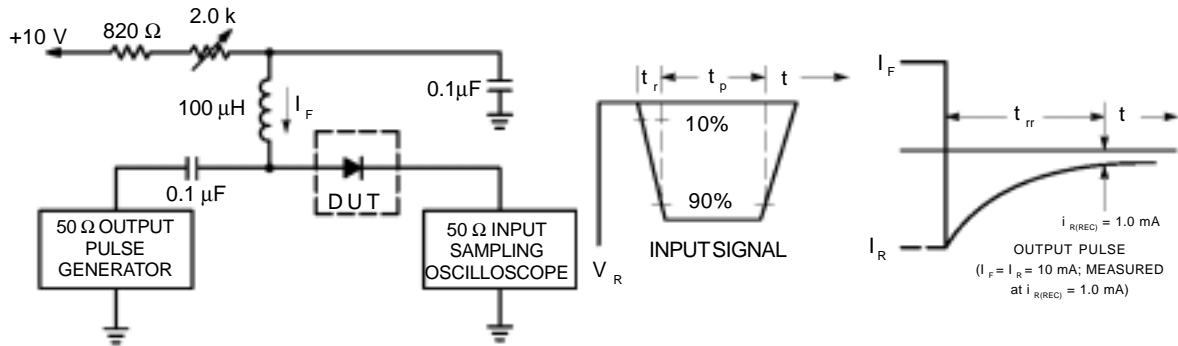
## OFF CHARACTERISTICS

Reverse Voltage Leakage Current ( $V_R = 75 \text{ Vdc}$ ) ( $V_R = 75 \text{ Vdc}, T_J = 150^\circ\text{C}$ ) ( $V_R = 25 \text{ Vdc}, T_J = 150^\circ\text{C}$ )	$I_R$	—	1.0 50 30	$\mu\text{Adc}$
Reverse Breakdown Voltage ( $I_{BR} = 100 \mu\text{Adc}$ )	$V_{(BR)}$	75	—	Vdc
Forward Voltage ( $I_F = 1.0 \text{ mAdc}$ ) ( $I_F = 10 \text{ mAdc}$ ) ( $I_F = 50 \text{ mAdc}$ ) ( $I_F = 150 \text{ mAdc}$ )	$V_F$	—	715 855 1000 1250	mV
Diode Capacitance ( $V_R = 0, f = 1.0 \text{ MHz}$ )	$C_D$	—	2.0	pF
Forward Recovery Voltage ( $I_F = 10 \text{ mAdc}, t_r = 20 \text{ ns}$ )	$V_{FR}$	—	1.75	Vdc
Reverse Recovery Time ( $I_F = I_R = 10 \text{ mAdc}, R_L = 50 \Omega$ )	$t_{rr}$	—	4.0	ns
Stored Charge ( $I_F = 10 \text{ mAdc}$ to $V_R = 5.0 \text{ Vdc}, R_L = 500 \Omega$ )	$Q_s$	—	45	pC

## LBAS16BST5G



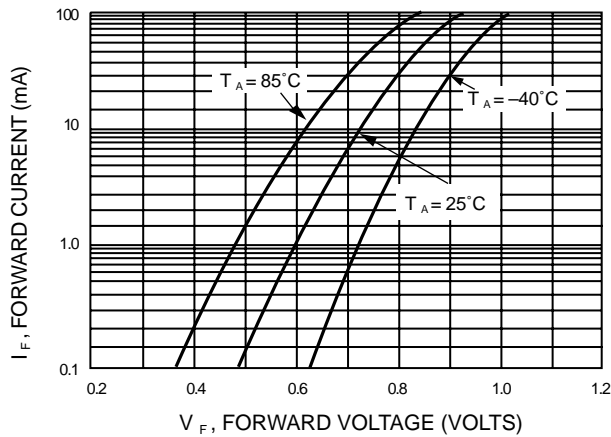
**LBAS16BST5G**



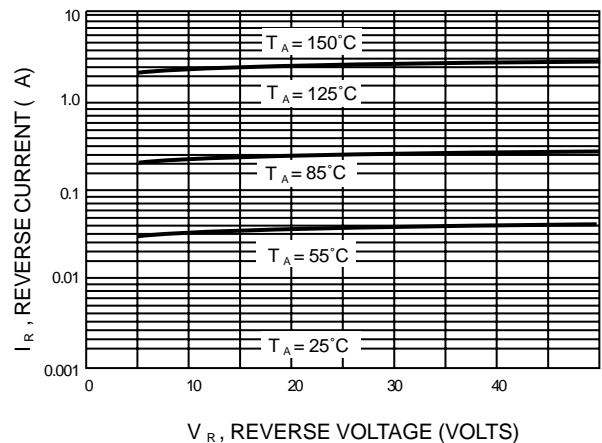
- Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current ( $I_F$ ) of 10mA.  
 2. Input pulse is adjusted so  $I_{R(peak)}$  is equal to 10mA.  
 3.  $t_p \gg t_{rr}$

**Figure 1. Recovery Time Equivalent Test Circuit**

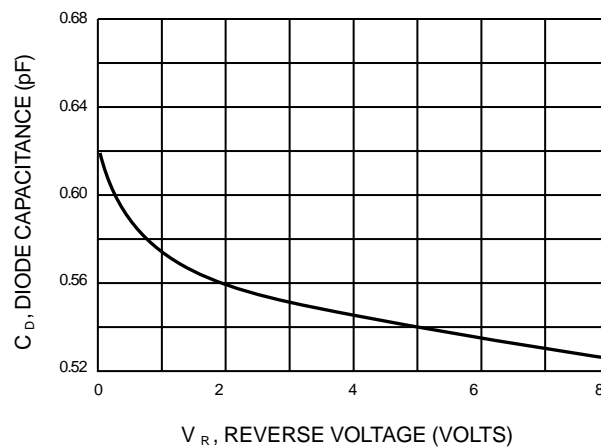
**TYPICAL CHARACTERISTICS**



**Figure 2. Forward Voltage**



**Figure 3. Leakage Current**

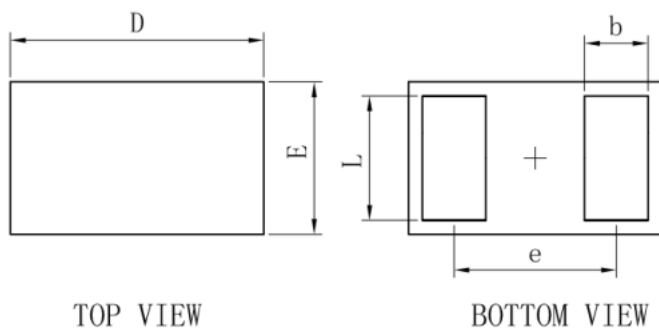


**Figure 4. Capacitance**

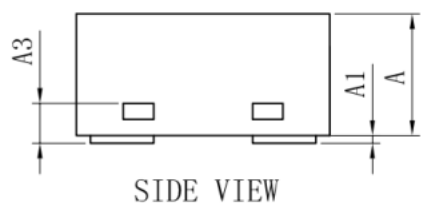
**LBAS16BST5G**

**OUTLINE AND DIMENSIONS**

**SOD882**

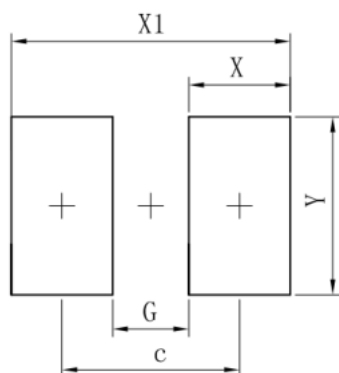


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Dim	Min	Typ	Max
D	0.95	1.00	1.05
E	0.55	0.60	0.65
e	-	0.64	-
L	0.44	0.49	0.54
b	0.20	0.25	0.30
A	0.43	0.48	0.53
A1	0	-	0.05
A3	0.127REF.		
All Dimensions in mm			



**SOLDERING FOOTPRINT**

**SOD882**



Dimensions	(mm)
c	0.70
G	0.30
X	0.40
X1	1.10
Y	0.70